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(54) **SEMICONDUCTOR MEMORY DEVICE**

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(57)

**ABSTRACT**

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A semiconductor memory device includes: a semiconductor substrate having a surface extending in an X direction and a Y direction; a circuit region formed on the semiconductor substrate and having at least one side extending in the Y direction; a guard ring line extending along the Y direction and opposed to the one side of the circuit region in the X direction; an element isolation region extending along the Y direction and formed between the one side of the circuit region and the guard ring line; and a dummy transistor disposed on an upper surface of the element isolation region. The dummy transistor includes: a main interconnection extending in the Y direction; and a branch interconnection extending from the main interconnection in the X direction.

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